

L21: (1148720) perpendicular \$2 orthogonal \$3
L22: (3134) 21 near 9 10
L23: (5005988) 13 16
L24: (5006008) 23 14
L25: (174121) 24 near 12 21
L28: (240008) 13 near 3 (10) 16 14
L27: (1883) 26 with 21
L28: (6) 27 and 9
L29: (568) (257/87.89).CCLS.
L30: (2278) (257/59.72).CCLS.
L32: (2778) 29 30
L33: (44) 27 and 32
L31: (63) 28 and 30
L34: (61164) (SRAM static adj3 memory static: adj RAM)
L35: (1429) 34 with 3
L38: (34) 27 and 35
L37: (2487147) parallel "same" adj direction
L38: (11875) 28 with 37
L39: (742) 38 same 6
L41: (154257) lcd
L42: (14) 38 and 41
L40: (21) 38 and 9
L43: (580634) offset
L44: (395) 17 with 43
L45: (1013) same 44

 Failed

Save

3 same 44

Sept 2004

	U	Y	Inventor	Document	Issue	P	Title	Current	Current XBRL	Retrieval	S	C	P	3	4	Image	Doc.	P
1			Zhang, Hongy	US 2003020	2003:1	2	Semiconductor display devices and applicati	257/59	257/E21.70		F	F	F	F	F		US 2003020	
2			So, Woo You	US 2002012	2002:0	1	Method of manufacturing CMOS thin film tra	438/373	257/E21.70		F	F	F	F	F		US 2002012	
3			So, Woo You	US 8753235	2004:0	1	Method of manufacturing CMOS thin film tra	438/373	438/278		F	F	F	F	F		US 8753235	
4			Zhang, Hongy	US 6614052	2003:0	2	Semiconductor display devices and applicati	257/59	257/350		F	F	F	F	F		US 6614052	
5			Ishiguro, Hide	US 6306683	2001:1	2	Method of manufacturing semiconductor dev	438/148	257/E21.41		F	F	F	F	F		US 6306683	
6			Kobayashi, K	US 6148930	2000:1	2	Method of fabricating an active-matrix liquid	438/154	257/E21.70		F	F	F	F	F		US 6148930	
7			Zhang, Hongy	US 5849107	1999:0	3	Semiconductor device and method of fabrica	257/347	257/348		F	F	F	F	F		US 5849107	
8			Maegawa, S	US 5821585	1998:1	2	Thin film transistor and manufacturing meth	257/347	257/348		F	F	F	F	F		US 5821585	
9			Kobayashi, K	US 5767930	1998:0	2	Active-matrix liquid crystal display and fabri	349/42	257/408		F	F	F	F	F		US 5767930	
10			Koyama, Jun	US 5764206	1998:0	1	Drive circuit and method for designing the sa	345/80	257/58		F	F	F	F	F		US 5764206	